



S/N 10/765,619

PATENT

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Kie Y. Ahn et al.

Examiner: Asok K Sarkar

Serial No.: 10/765,619

Group Art Unit: 2829

Filed: January 27, 2004

Docket No.: 1303.033US2

Title: HIGH-QUALITY PRASEODYMIUM GATE DIELECTRICS (As Amended)

---

**AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111**

MS Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

This responds to the Office Action mailed on December 10, 2004. Please amend the above-identified patent application as follows.

**IN THE TITLE**

Please amend the title as follows:

~~LOW-TEMPERATURE GROWN~~ HIGH-QUALITY ~~ULTRA-THIN~~ PRASEODYMIUM  
GATE DIELECTRICS